

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-6.9	A
		T <sub>A</sub> = +70°C		-5.8	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	-24	A

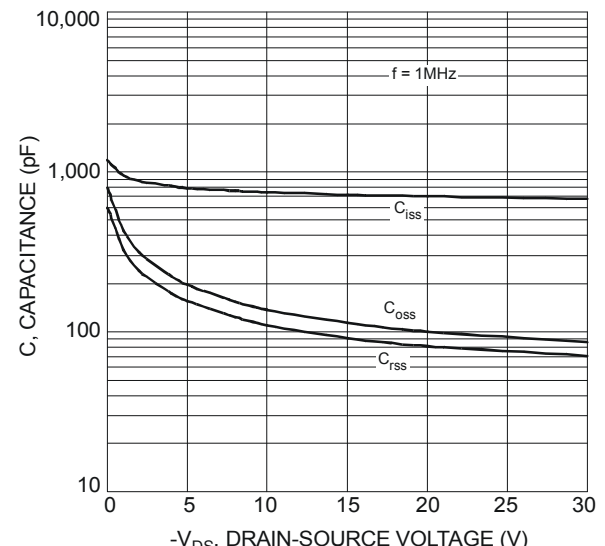
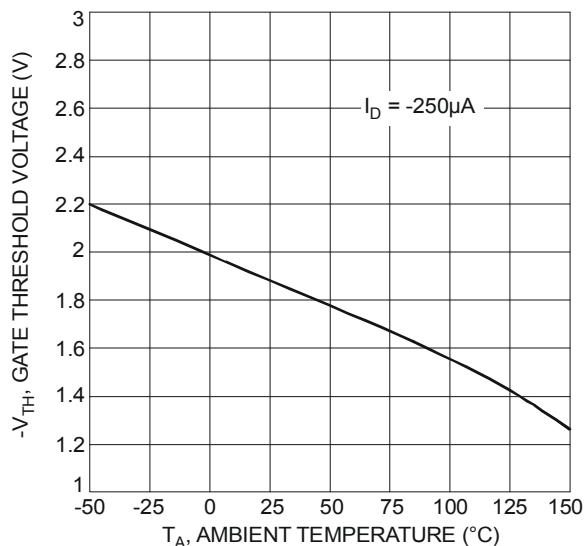
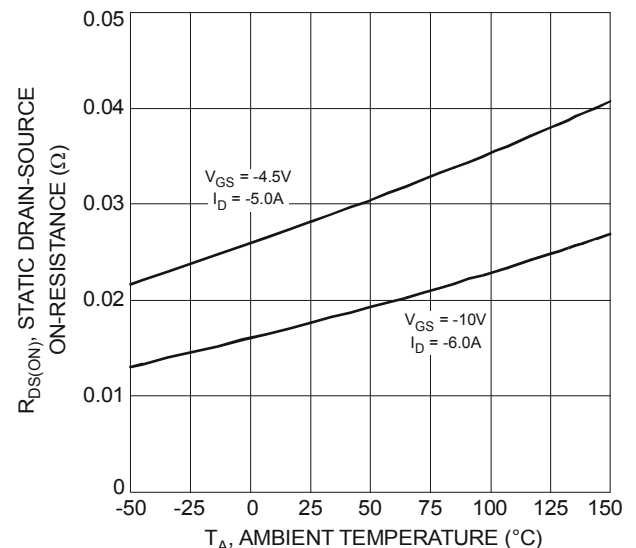
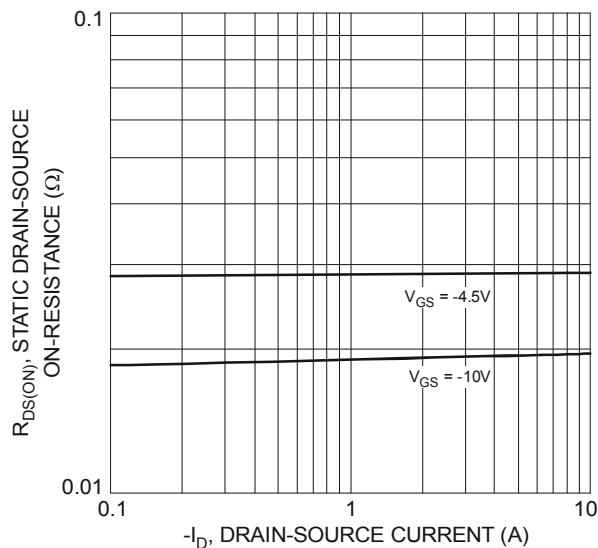
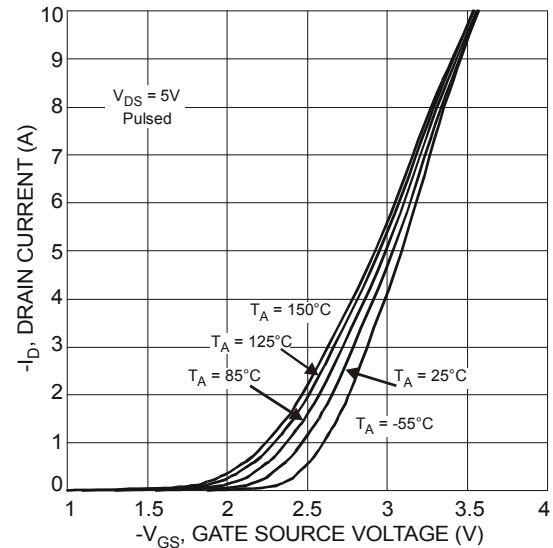
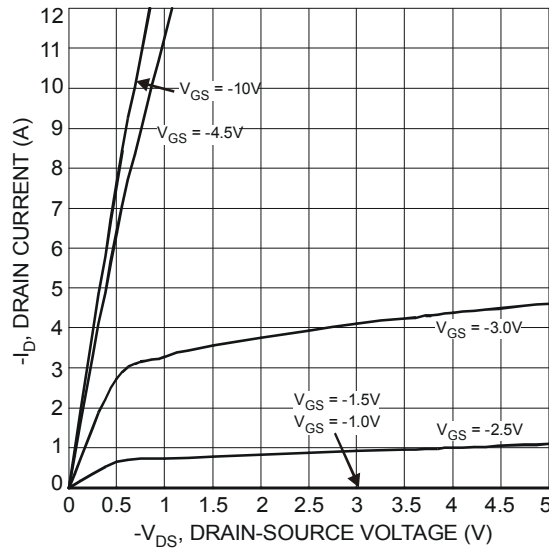
**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	50	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100 ±800	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V V <sub>GS</sub> = ±25V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-1	-1.7	-2.1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	45	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -6.0A
		—	—	65		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -5.0A
Forward Transconductance	g <sub>fs</sub>	—	8	—	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -5.3A
Diode Forward Voltage (Note 7)	V <sub>SD</sub>	-0.5	—	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.7A
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	722	—	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	114	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	92	—	pF	
Gate Resistance	R <sub>G</sub>	—	3.3	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V f = 1.0MHz
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge	Q <sub>G</sub>	—	6.8	—	nC	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -6A
	Q <sub>G</sub>	—	13.7	—		
Gate-Source Charge	Q <sub>GS</sub>	—	1.6	—	nC	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -6A
Gate-Drain Charge	Q <sub>GD</sub>	—	4.2	—		
Turn-On Delay Time	t <sub>d(on)</sub>	—	6.4	—	ns	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -1A, R <sub>G</sub> = 6.0Ω
Rise Time	t <sub>r</sub>	—	5.3	—		
Turn-Off Delay Time	t <sub>d(off)</sub>	—	26.5	—		
Fall Time	t <sub>f</sub>	—	14.7	—		

- Notes: 5. Device mounted on 2 oz. 1" x 1" Copper pads on 2" x 2" FR-4 PCB.  
6. Pulse width ≤10μs, Duty Cycle ≤1%.  
7. Short duration pulse test used to minimize self-heating effect.



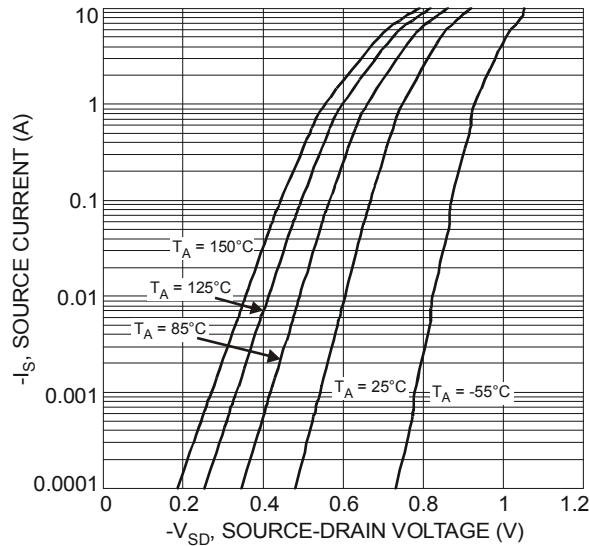
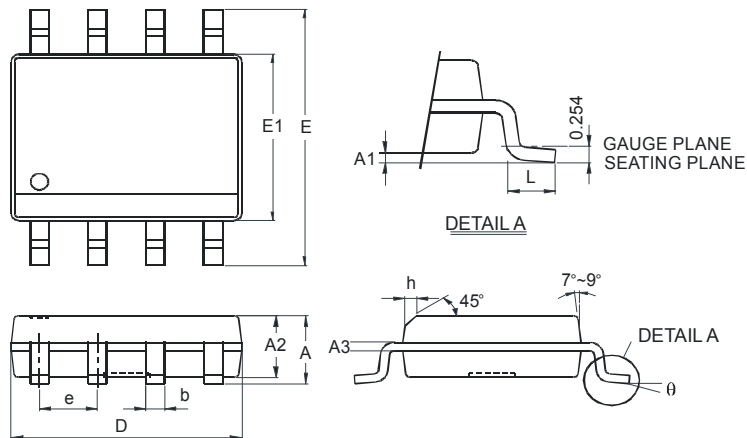


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

## Package Outline Dimensions

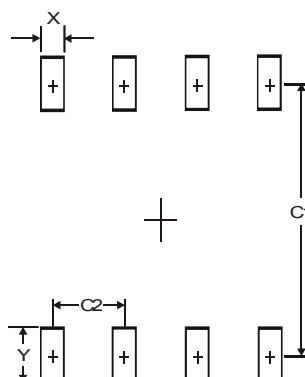
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
$\theta$	0°	8°
All Dimensions in mm		

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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